

In the example of Fig. 97 and Fig. 98, the source diffusion layer 710 is disposed so that the semiconductor substrate 100 is connected to the island-like semiconductor layer 110, and the diffusion layer 720 is disposed so that the active regions of adjacent transistors are connected to each other in the island-like semiconductor layer 110. The island-like semiconductor layer 110 and the semiconductor substrate 100 becomes in an electrically floating state owing to a depletion layer formed on a semiconductor substrate or an island-like semiconductor layer of a PN junction formed between the source diffusion layer 710 and the semiconductor substrate 100 or the island-like semiconductor layer 110 by a difference between a potential given to the source diffusion layer 710 and a potential given to the semiconductor substrate 100 at reading or at erasing. The active regions of the adjacent transistors are electrically insulated from each other owing to a depletion layer formed in the island-like semiconductor of the PN junction formed between the diffusion layer 720 and the island-like semiconductor layer 110 by a difference between the potential given to the diffusion layer 720 and a potential given to the island-like semiconductor layer 110.

#### IN THE CLAIMS

Please cancel non-elected claims 20-28, without prejudice in view of the Restriction Requirement.